

**Amendments to the Specification:**

*Please amend the fourth full paragraph on page 15 ( lines 20-26) to read as follows:*

“For QWs, charge carriers will be required to be injected into and extracted from subbands in the active-layers that may be energetically distant from the conduction- and/or valence-band edges of the bulk material that the active-layer is made of. Because the energy difference between the “excited subband” and the “ground subband” is dependent on the energy of the photons to be absorbed or emitted, this issue is important for Inter-Subband Transitions (i.e., Quantized Interband Transitions) (FIGs. **3B, 3C, 3D**), and it is even important so for Intra-Subband Transitions in the conduction-band (i.e., Electron Intersubband Transitions) (FIGs. **4B, 4C, 4D**), or in the valence-band (i.e., Hole Intersubband Transitions) (FIGs. **5B, 5C, 5D**).”